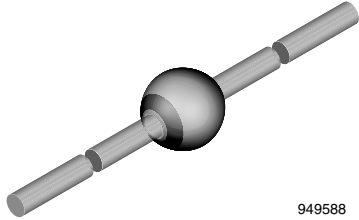


Standard Avalanche Sinterglass Diode



949588

FEATURES

- Glass passivated junction
- Hermetically sealed package
- Controlled avalanche characteristics
- Low reverse current
- High surge current loading
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition


RoHS
 COMPLIANT
 HALOGEN
FREE

MECHANICAL DATA

Case: SOD-64

Terminals: plated axial leads, solderable per MIL-STD-750, method 2026

Polarity: color band denotes cathode end

Mounting position: any

Weight: approx. 858 mg

APPLICATIONS

- Rectification diode, general purpose

PARTS TABLE		
PART	TYPE DIFFERENTIATION	PACKAGE
1N5624	$V_R = 200\text{ V}$; $I_{FAV} = 3\text{ A}$	SOD-64
1N5625	$V_R = 400\text{ V}$; $I_{FAV} = 3\text{ A}$	SOD-64
1N5626	$V_R = 600\text{ V}$; $I_{FAV} = 3\text{ A}$	SOD-64
1N5627	$V_R = 800\text{ V}$; $I_{FAV} = 3\text{ A}$	SOD-64

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified)					
PARAMETER	TEST CONDITION	PART	SYMBOL	VALUE	UNIT
Reverse voltage = repetitive peak reverse voltage	See electrical characteristics	1N5624	$V_R = V_{RRM}$	200	V
		1N5625	$V_R = V_{RRM}$	400	V
		1N5626	$V_R = V_{RRM}$	600	V
		1N5627	$V_R = V_{RRM}$	800	V
Peak forward surge current	$t_p = 10\text{ ms}$, half sinewave		I_{FSM}	100	A
Repetitive peak forward current			I_{FRM}	18	A
Average forward current			I_{FAV}	3	A
Pulse avalanche peak power	$t_p = 20\text{ }\mu\text{s}$, half sine wave, $T_j = 175\text{ }^\circ\text{C}$		P_R	1000	W
Pulse energy in avalanche mode, non repetitive (inductive load switch off)	$I_{(BR)R} = 1\text{ A}$, $T_j = 175\text{ }^\circ\text{C}$		E_R	20	mJ
i^2t -rating			i^2t	40	A^2s
Junction and storage temperature range			$T_j = T_{stg}$	- 55 to + 175	$^\circ\text{C}$

MAXIMUM THERMAL RESISTANCE ($T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Junction ambient	$l = 10\text{ mm}$, $T_L = \text{constant}$	R_{thJA}	25	K/W
	On PC board with spacing 25 mm	R_{thJA}	70	K/W

1N5624, 1N5625, 1N5626, 1N5627

Vishay Semiconductors Standard Avalanche Sinterglass Diode



ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 3\text{ A}$		V_F	-	-	1	V
Reverse current	$V_R = V_{RRM}$		I_R	-	0.1	1	μA
	$V_R = V_{RRM}, T_j = 100\text{ }^{\circ}\text{C}$		I_R	-	5	10	μA
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}, t_p/T = 0.01, t_p = 0.3\text{ ms}$		$V_{(BR)}$	-	-	1600	V
Diode capacitance	$V_R = 4\text{ V}, f = 1\text{ MHz}$		C_D	-	40	60	pF
Reverse recovery time	$I_F = 0.5\text{ A}, I_R = 1\text{ A}, i_R = 0.25\text{ A}$		t_{rr}	-	3.5	5	μs
	$I_F = 1\text{ A}, di/dt = 5\text{ A}/\mu\text{s}, V_R = 50\text{ V}$		t_{rr}	-	4.5	7.5	μs
Reverse recovery charge	$I_F = 1\text{ A}, di/dt = 5\text{ A}/\mu\text{s}$		Q_{rr}	-	8	12	μC

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

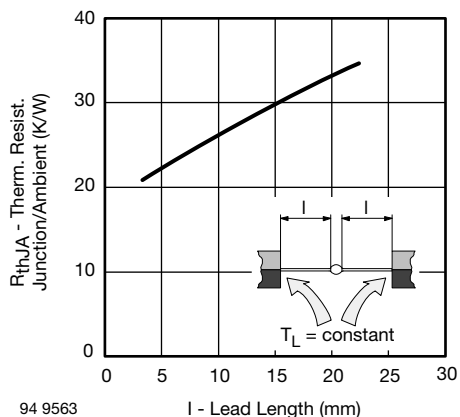


Fig. 1 - Max. Thermal Resistance vs. Lead Length

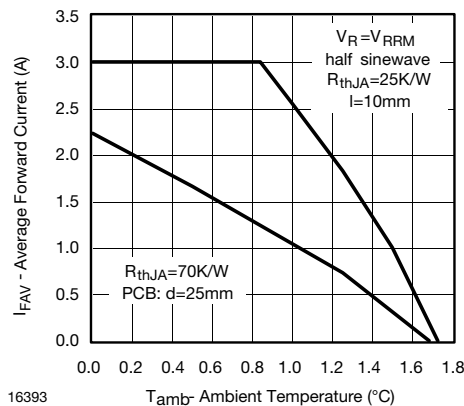


Fig. 3 - Max. Average Forward Current vs. Ambient Temperature

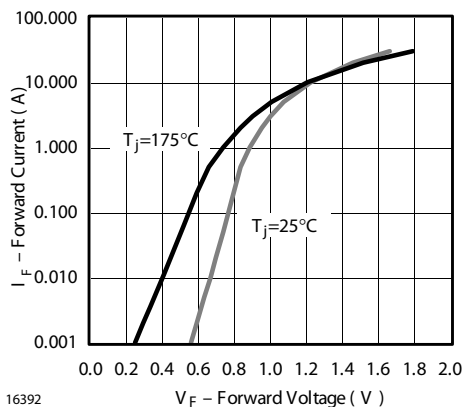


Fig. 2 - Forward Current vs. Forward Voltage

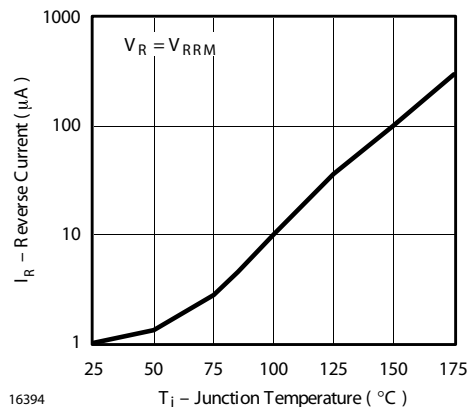


Fig. 4 - Reverse Current vs. Junction Temperature

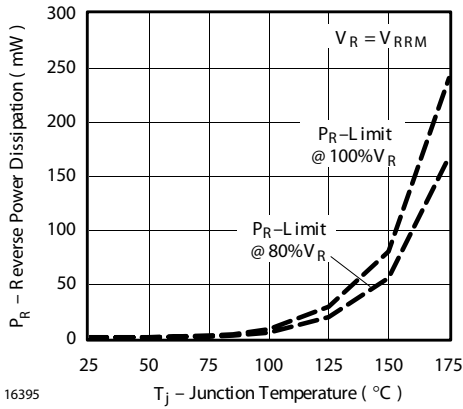


Fig. 5 - Max. Reverse Power Dissipation vs. Junction Temperature

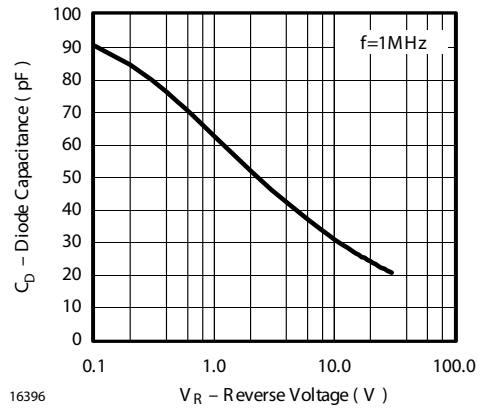
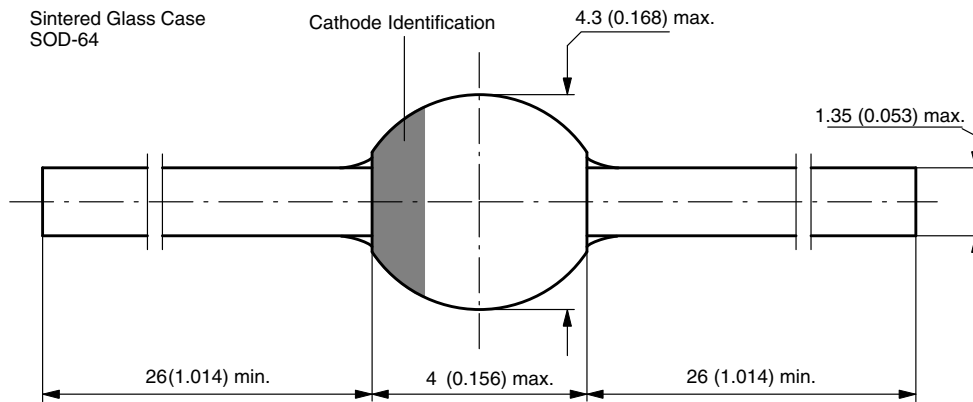


Fig. 6 - Diode Capacitance vs. Reverse Voltage

PACKAGE DIMENSIONS in millimeters (inches): SOD-64



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 94 9587



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